

WHAT IS CLAIMED IS:

1. A group III nitride compound semiconductor light-emitting device comprising:

a semiconductor laminate portion containing a light-emitting layer; and

a groove formed in said semiconductor laminate portion so as to extend from a light emission observation surface of said semiconductor laminate portion to reach at least said light-emitting layer.

2. A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said groove is distributed equally in said light emission observation surface.

3. A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said groove is formed by etching.

4. A group III nitride compound semiconductor light-emitting device according to claim 3, wherein an n-type seat electrode-forming surface is provided at a level equal to a bottom of said groove.

5. A group III nitride compound semiconductor

light-emitting device comprising:

a substrate;

a semiconductor laminate being laminated on said substrate and comprising a plurality of group III nitride compound semiconductor layers, said semiconductor laminate including at least a light-emitting region; and

a groove formed in said semiconductor laminate so as to extend within a plane of a light emission observation surface of said semiconductor laminate, said groove having a depth to reach said light-emitting region to thereby reveal said light-emitting region on a side surface of said groove.

6. A group III nitride compound semiconductor light-emitting device according to claim 5, wherein a width of said groove is in a range of from 0.5 to 30 μm .

7. A group III nitride compound semiconductor light-emitting device according to claim 5, further comprising an n-type seat electrode-forming surface formed in said semiconductor laminate and adapted to mount an n-type seat electrode, wherein a bottom surface of said groove is located substantially at the same height level as said n-type seat electrode-forming surface.

8. A group III nitride compound semiconductor

light-emitting device according to claim 5, further comprising a p-type seat electrode and an n-type seat electrode, and said semiconductor laminate has a plurality of current diffusion paths formed between said p-type seat electrode and said n-type seat electrode and each being divided by said groove, all of said current diffusion paths having substantially same lengths and same widths.

9. A group III nitride compound semiconductor light-emitting device comprising:
a substrate; and
a plurality of semiconductor layer blocks formed on said substrate, each of said semiconductor layer blocks having a light-emitting region revealed on a side surface thereof.

10. A group III nitride compound semiconductor light-emitting device according to claim 9, further comprising a p-type seat electrode formed on one of said semiconductor layer blocks and an auxiliary electrode extending from said p-type seat electrode to another semiconductor layer block.

11. A group III nitride compound semiconductor light-emitting device according to claim 10, further comprising an insulating layer formed between said semiconductor layer block and said auxiliary electrode.